

Technical Data Data Sheet N1567, Rev. - **Green Products**

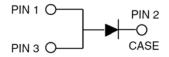
STF30100S SCHOTTKY RECTIFIER

Applications:

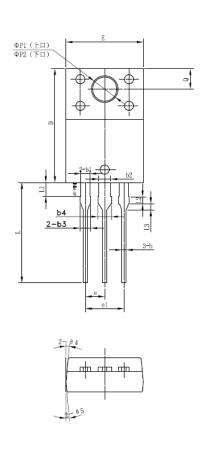
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

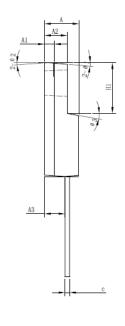
Features:

- 150°C T_J operation
- Center tap configuration
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot



Mechanical Dimensions (In mm) and Marking:





SYMBOL	MIN.	TYP.	MAX.
Α	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
С	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
е		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

Remark: Lead burr spec is 0.1mm Max.

ITO-220AB

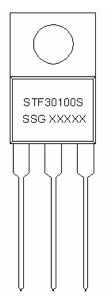
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Marking Diagram:



Where XXXXX is YYWWL

ST = Device Type F = Package type

30 = Forward Current (30A) 100 = Reverse Voltage (100V) S = Internal Structure

SSG = SSG YY = Year

WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping	
STF30100S	ITO-220AB	FOr co/tube	
	(Pb-Free)	50pcs/ tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =100°C, rectangular wave form	30	А
Peak One Cycle Non-Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	300	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop(per	V_{F1}	@ 30A, Pulse, T _J = 25 °C	0.90	V
leg)*	V_{F2}	@ 30A, Pulse, T _J = 125 °C	0.78	V
Reverse Current (per	I _{R1}	$@V_R = \text{rated } V_R$	1	mA
leg)*		T _J = 25 °C		
	I_{R2}	$@V_R = \text{rated } V_R$	75	mA
		T _J = 125 °C		
Junction Capacitance	C_{T}	$@V_R = 5V, T_C = 25 ^{\circ}C$	1000	pF
(per leg)	OT	f _{SIG} = 1MHz	1000	Рі
Voltage Rate of Change	dv/dt	-	10,000	V/μs

Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case(per leg)*	$R_{ heta JC}$	DC operation	5.0	°C/W
Approximate Weight	wt	-	2	g
Case Style		ITO-220AB		·

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